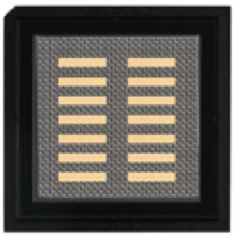
EB-BB-100-0808-10

HIGH POWER DIODE BAR LASER CHIP



	Unit	Min	Typ	Max
Optical				
Center Wavelength	nm		808	
Wavelength Tolerance	nm		±10	
Output Power	W	100		
Fast-axis Divergence	Deg		65	75
Slow-axis Divergence	Deg		10	
Spectral Width (FWHM)	nm		3	4
Polarization	TM/TE		TE	
Wavelength Temperature Coefficient	nm/℃		0.28	
Electrical				
Power Conversion Efficiency	%		55	
Slope Efficiency	W/A		1.25	
Threshold Current	A		15	
Operating Current	A		105	110
Operating Voltage	V		1.8	
Pulse Width	us		-	
Pulse frequency	Hz		-	
Pulse duty cycle	%		-	
Geometric Size				
Number of Emitters	#		49	
Emitter Width	μm		100	
Emitter Pitch	μm		200	
Fill Factor	%		50	
Cavity Length	mm		1.5	
Bar Thickness	μm		130	
Bar Length	mm	9.98	10	10.02
Thermal				
Operating Temperature	℃		25	
Storage Temperature	℃		-40~80	
Flow Velocity	L/min		0.25	

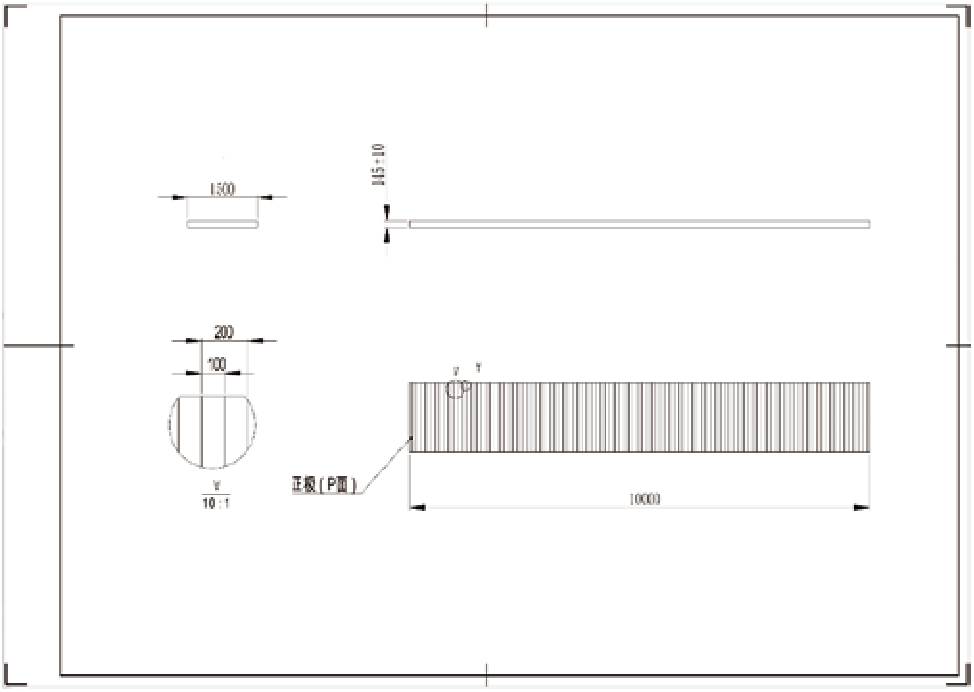
Remarks

1.Explanation of Item Number： EB (Everbright In Short) - BB (Bare Bar)—100 (Output Power) - 0808 (Center Wavelength) - 10 (Wavelength Tolerance)

2.Above Data Test at 25℃, Unless otherwise stated.

3.Please avoid operation and storage in the condensation enviroment. If exceed operating temperature, the device lifetime will be inpacted.

4. Lifetime reduced if exceed nominal output power.



Dimension appearance

Product Features

- High Reliability
- High Efficiency
- High Power

Application

- Industrial Pump
- Laser Equipment
- R&D
- Biomedical